PCB   24

SHARP

Integrated Circuits Group

LH52256CH-85LL
256K SRAM

(Model No.: LH525CL2)

Spec No.: EL095124
Issue Date: June 3, 1997

conditions and precautions.

(1) The products covered herein are designed and manufactured for the following application areas. When using the products covered herein for the equipment listed in Paragraph (2), even for the following application areas, be sure to observe the precautions given in Paragraph (2). Never use the products for the equipment listed in Paragraph (3).

- Office electronics
- Instrumentation and measuring equipment
- Machine tools
- Audiovisual equipment
- Home appliances
- Communication equipment other than for trunk lines

(2) Those contemplating using the products covered herein for the following equipment which demands high reliability, should first contact a sales representative of the company and then accept responsibility for incorporating into the design fail-sale operation, redundancy, and other appropriate measures for ensuring reliability and safety of the equipment and the overall system.

- Control and safety devices for airplanes, trains, automobiles, and other transportation equipment
- Mainframe computers
- Traffic control systems
- Gas leak detectors and automatic cutoff devices
- Rescue and security equipment
- Other safety devices and safety equipment, etc.

(3) Do not use the products covered herein for the following equipment which demands extremely high performance in terms of functionality, reliability, or accuracy.
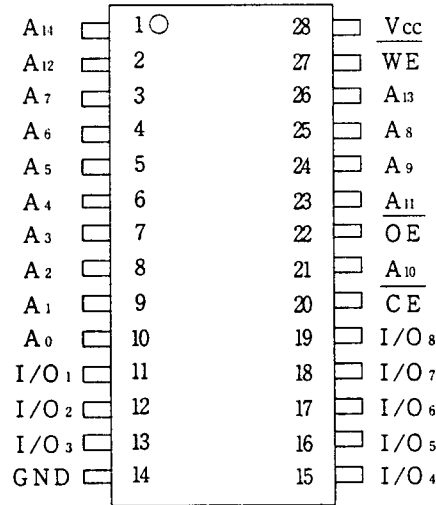
- Aerospace equipment
- Communications equipment for trunk lines
- Control equipment for the nuclear power industry
- Medical equipment related to life support, etc.

(4) Please direct all queries and comments regarding the interpretation of the above three Paragraphs to a sales representative of the company.

● Please direct all queries regarding the products covered herein to a sales representative of the company.

○Access Time   ・・・・ $8\,5$ ns (Max.)

○Operating current   ・・・・ $4\,0$ mA (Max.)

                         ・・・・ $1\,0$ mA (Max. t_{RC}. $t_{WC}=1\,\mu s$)

○Standby current   ・・・・ $4\,0$ μA (Max.)

○Data retention current   ・・・・ $1.\,0$ μA (Max. $V_{CCDR}=3\,V, Ta=2\,5°C$)

○Wide operating voltage range   ・・・・ $4.\,5\,V$ to $5.\,5\,V$

○Operating temperature   ・・・・ $-4\,0°C$ to $+8\,5°C$

○Fully static operation

○Three-state output

○Not designed or rated as radiation hardened

○$2\,8$ pin DIP (DIP28$-$P$-6\,0\,0$) plastic package

○N-type bulk silicon

2. Pin Configuration

A_{14}	1 ○ 28	V_{cc}
A_{12}	2 27	$\overline{WE}$
A_7	3 26	A_{13}
A_6	4 25	A_8
A_5	5 24	A_9
A_4	6 23	A_{11}
A_3	7 22	$\overline{OE}$
A_2	8 21	A_{10}
A_1	9 20	$\overline{CE}$
A_0	10 19	I/O_8
I/O_1	11 18	I/O_7
I/O_2	12 17	I/O_6
I/O_3	13 16	I/O_5
GND	14 15	I/O_4

(Top View)

Pin Name	Function
A_0 to A_{14}	Address inputs
$\overline{CE}$	Chip enable
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
I/O_1 to I/O_8	Data inputs/outputs
V_{cc}	Power supply
GND	Ground

L	L	*	Write	Data Input	Active (I_{cc})

(*=Don't Care, L=Low, H=High)

4. Block Diagram
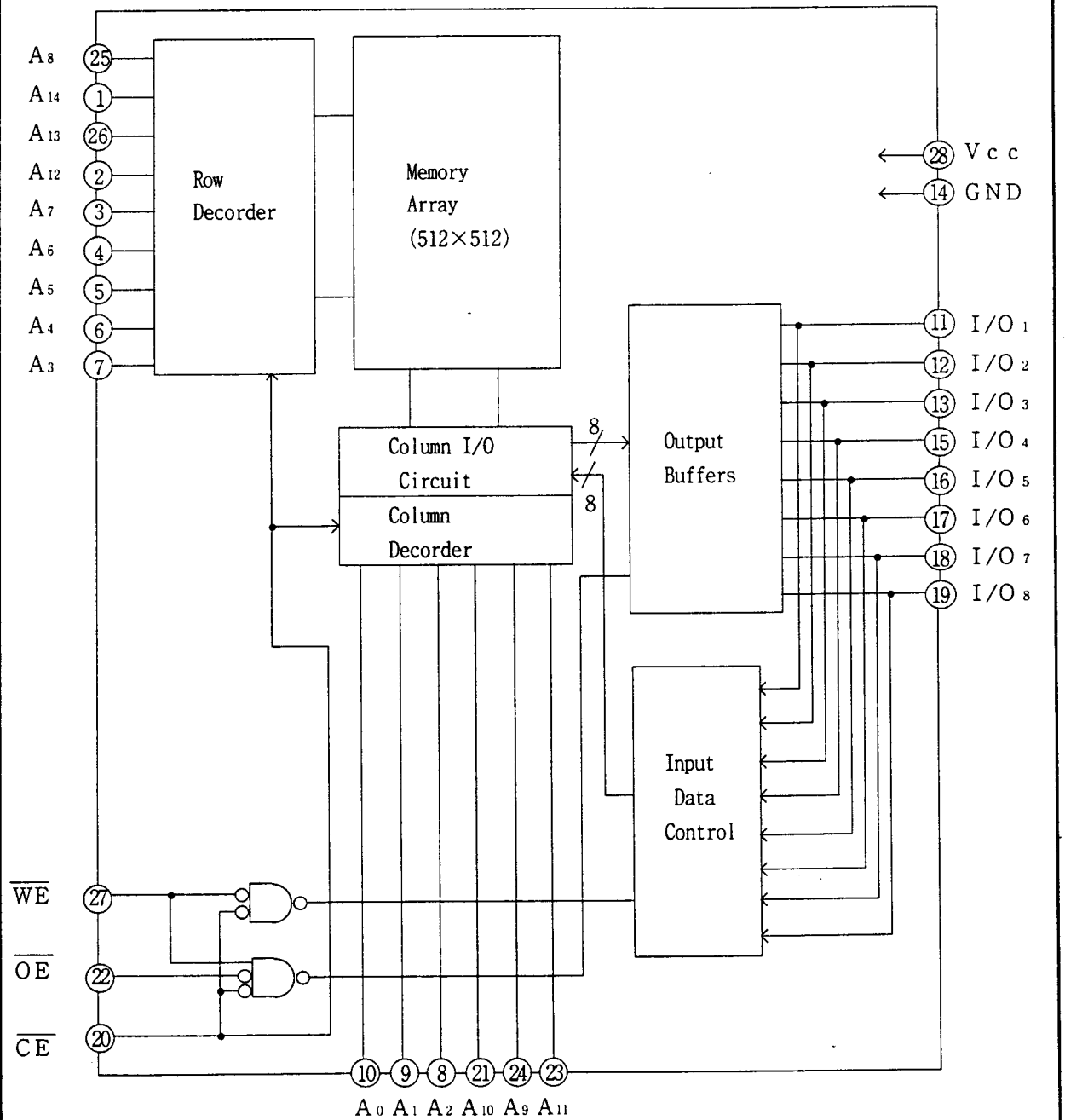
		Storage temperature	T_{stg}	-65 to $+150$	℃

Note) *1.The maximum applicable voltage on any pin with respect to GND.
　　　*2.Undershoot of $-3.0V$ is allowed width of pluse bellow 50ns.

6.Recommended DC Operating Conditions

(Ta= -40 ℃ to $+85$ ℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{cc}	4.5	5.0	5.5	V
Input voltage	V_{IH}	2.2		$V_{cc}+0.5$	V
	V_{IL}	-0.5 (*3)		0.8	V

Note) *3.Undershoot of $-3.0V$ is allowed width of pluse below 50ns.

7.DC Electrical Characteristics

(Ta= -40 ℃ to $+85$ ℃, Vcc= 4.5 V to 5.5 V)

Parameter	Symbol	Conditions	Min.	Typ. (*4)	Max.	Unit
Input leakage current	I_{LI}	V_{IN} =0V to V_{cc}	-1.0		1.0	μA
Output leakage current	I_{LO}	$\overline{CE}$ =V_{IH} or $\overline{OE}$ =V_{IH} $V_{I/O}$ =0V to V_{cc}	-1.0		1.0	μA
Operating supply current	I_{CC}	Minimum cycle V_{IN} =V_{IL} or V_{IH}, $I_{I/O}$ =0mA, $\overline{CE}$ =V_{IL}		25	40	mA
	I_{CC1}	t_{RC}, t_{WC} =1μ s V_{IN} =V_{IL} or V_{IH}, $I_{I/O}$ =0mA, $\overline{CE}$ =V_{IL}			10	mA
Standby current	I_{SB}	$\overline{CE}$ $\geqq V_{cc}-0.2V$		0.6	40	μA
	I_{SB1}	$\overline{CE}$ =V_{IH}			3	mA
Output voltage	V_{OL}	I_{OL}= 2.1mA			0.4	V
	V_{OH}	I_{OH}=-1.0mA	2.4			V

Note) *4.Typical values at Vcc=5.0V, Ta=25℃.

Parameter		
Input and output timing Ref. level		1.5 V
Output load		1 TTL + C_L (100 pF) (*5)

Note) *5. Including scope and jig capacitance.

Read cycle

(Ta= −40℃ to +85℃, Vcc= 4.5 V to 5.5 V)

Parameter	Symbol	Min.	Max.	Unit	
Read cycle time	t_{RC}	85		ns	
Address access time	t_{AA}		85	ns	
$\overline{CE}$ access time	t_{ACE}		85	ns	
Output enable to output valid	t_{OE}		35	ns	
Output hold from address change	t_{OH}	10		ns	
$\overline{CE}$ Low to output active	t_{LZ}	10		ns	*6
$\overline{OE}$ Low to output active	t_{OLZ}	5		ns	*6
$\overline{CE}$ High to output in High impedance	t_{HZ}	0	30	ns	*6
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0	30	ns	*6

Write cycle

(Ta= −40℃ to +85℃, Vcc= 4.5 V to 5.5 V)

Parameter	Symbol	Min.	Max.	Unit	
Write cycle time	t_{WC}	85		ns	
$\overline{CE}$ Low to end of write	t_{CW}	55		ns	
Address valid to end of write	t_{AW}	55		ns	
Address setup time	t_{AS}	0		ns	
Write pluse width	t_{WP}	40		ns	
Write recovery time	t_{WR}	0		ns	
Input data setup time	t_{DW}	30		ns	
Input data hold time	t_{DH}	0		ns	
$\overline{WE}$ High to output active	t_{OW}	5		ns	*6
$\overline{WE}$ Low to output in High impedance	t_{WZ}	0	30	ns	*6
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0	30	ns	*6

Note) *6. Active output to High impedance and High impedance to output active tests
specified for a ±200mV transition from steady state levels into the test load.

Data Retention supply current	I $_{CCDR}$	V$_{CCDR}$=3 V	Ta=25℃		0.3	1.0	μA
			Ta=70℃			15	μA
			$\overline{CE}$ ≥ V$_{CCDR}$−0.2 V (*5)			20	μA
Chip enable setup time	t$_{CDR}$			0			n s
Chip enable hold time	t$_R$			(*8) t$_{RC}$			n s

Note) ＊7. Typical values at Ta=25℃

＊8. Read Cycle

10. Pin Capacitance

(Ta＝2 5℃, f＝1 MH z)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Input capacitance	C$_{IN}$	V$_{IN}$=0 V			7	p F	＊9
I/O capacitance	C$_{I/O}$	V$_{I/O}$=0 V			1 0	p F	＊9

Note) ＊9.This parameter is sampled and not production tested.
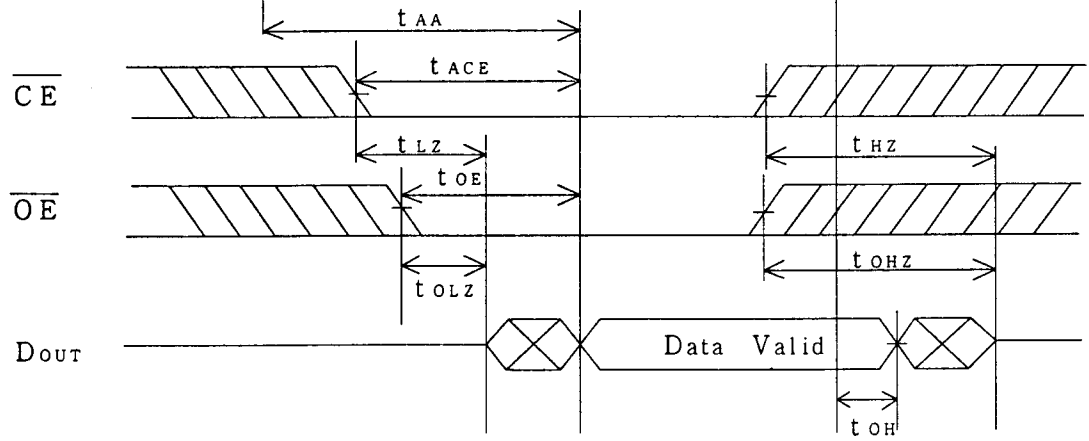
Note) *10. $\overline{WE}$ is high for Read cycle.

Write cycle timing chart — ($\overline{OE}$ Controlled)

Timing Diagram

$\overline{CE}$

t_{AW} t_{WR} (*14)

t_{CW} (*12)

$\overline{WE}$

t_{AS} (*13) t_{WP} (*11) t_{WR} (*14)

D_{OUT}

(*16) t_{WZ} t_{OW} (*17)

D_{IN}

t_{DW} t_{DH}

(*15) Data Valid
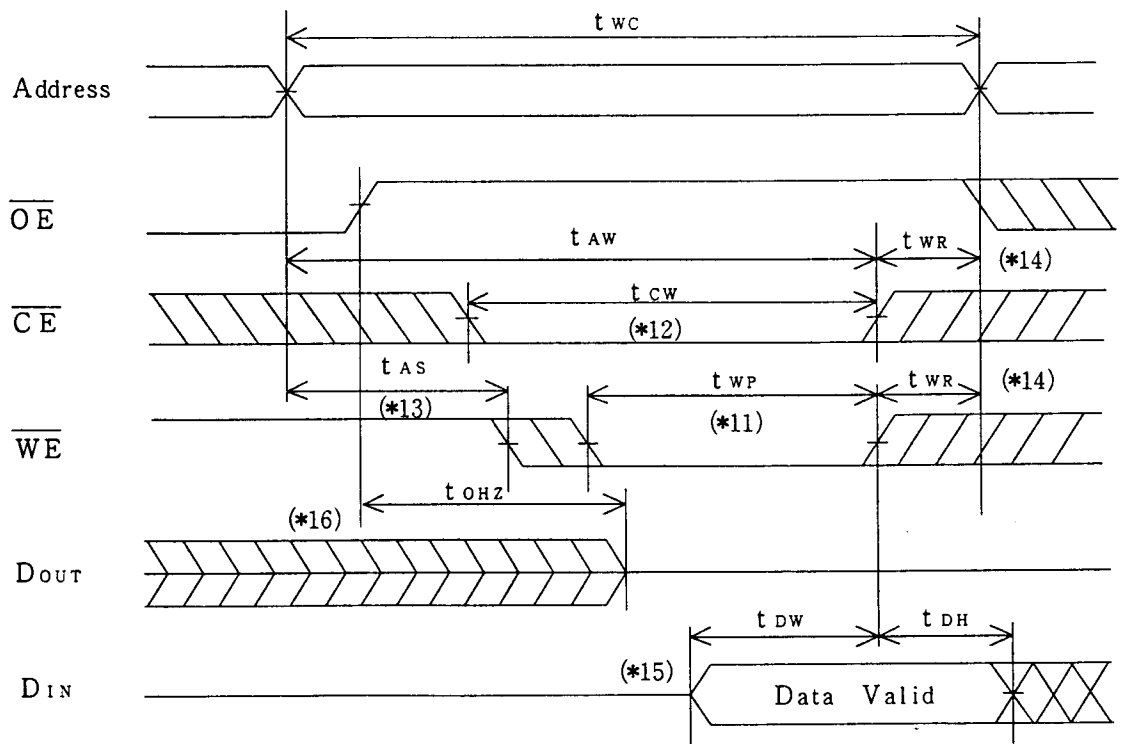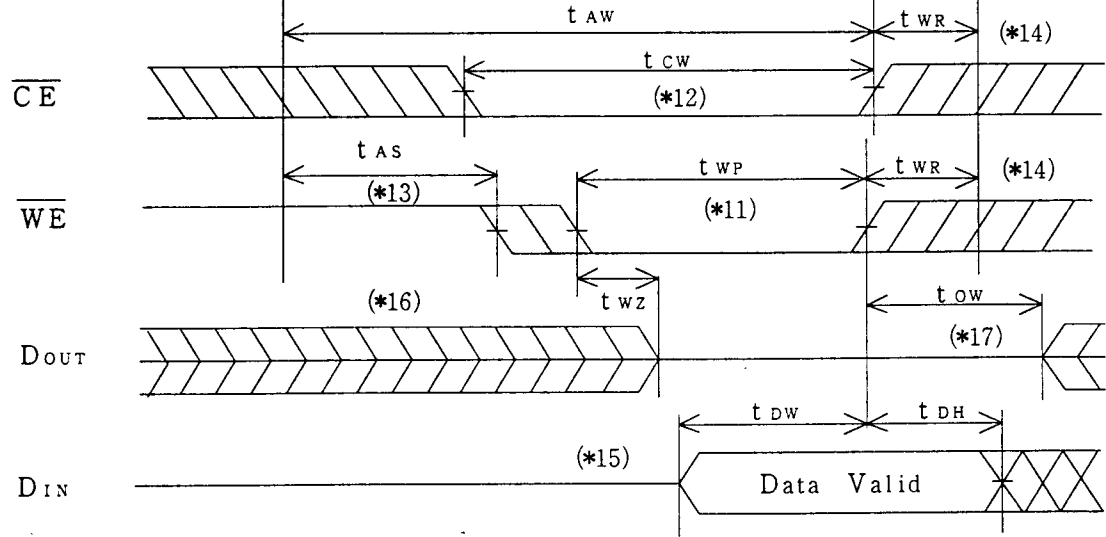
Note)
* 11. A write occurs during the overlap of a low $\overline{CE}$, and a low $\overline{WE}$,

A write begins at the latest transition among $\overline{CE}$ going low, and $\overline{WE}$ going low.

A write ends at the earliest transition among $\overline{CE}$ going high, and $\overline{WE}$ going high.

t_{WP} is measured from the beginning of write to the end of write.

* 12. t_{CW} is measured from the later of $\overline{CE}$ going low to the end of write.

* 13. t_{AS} is measured from the address valid to the beginning of write.

* 14. t_{WR} is measured from the end of write to the address change.

* 15. During this period, I/O pins are in the output state, therefore the input signals
of opposite phase to the outputs must not be applied.

* 16. If $\overline{CE}$ goes low simultaneously with $\overline{WE}$ going low or after $\overline{WE}$ going low,
the outputs remain in high impedance state.

* 17. If $\overline{CE}$ goes high simultaneously with $\overline{WE}$ going high or before $\overline{WE}$ going high,
the outputs remain in high impedance state.

V_{CC}

4.5 V

t_{CDR}

t_R

2.2 V
V_{CCDR}

$\overline{CE} \geqq V_{CCDR} - 0.2 V$

$\overline{CE}$

0 V
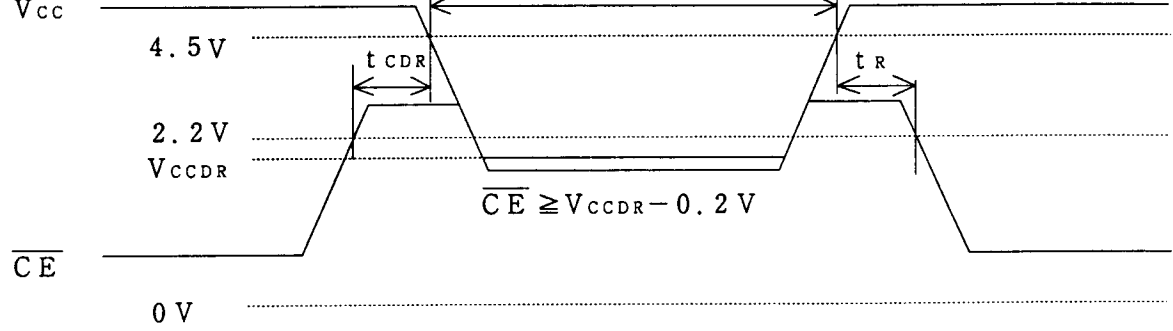
(2) Company name ： ＳＨＡＲＰ
(3) Date code
  (Example) Y Y   WW   ×××   Indicates the product was manufactured
                                      in the WWth week of 19YY.
                              └──→ Denotes the production ref.code (1~3)
                       └──────→ Denotes the production week.
                                      (01,02,03,・・・・・52,53)
                └─────────────→ Denotes the production year.
                                      (Lower two digits of the year.)
(4) The marking of "JAPAN" indicates the country of origin.
2－2. Marking layout
    Refer to drawing No.ＡＡ８５２
(This layout does not define the dimensions of marking character and marking position.)

3. Packing Specification
  3－1. Packing materials

Material Name	Material Specification	Purpose
Magazine	Anti-static treated plastic (15devices/magazine)	Packing of device
Stopper	Plastic or rubber	Fixing of device
Label	Paper	Indication of product name,quantity and date of manufacture.
Inner case	Cardboard (600devices/cace)	Fixing of magazine
Outer case	Cardboard	Outer packing of magazine

    (Devices shall be inserted into a magazine (sleeve) in the same direction.)
  3－2. Outline dimension of magazine (sleeve)
    Refer to attached drawing

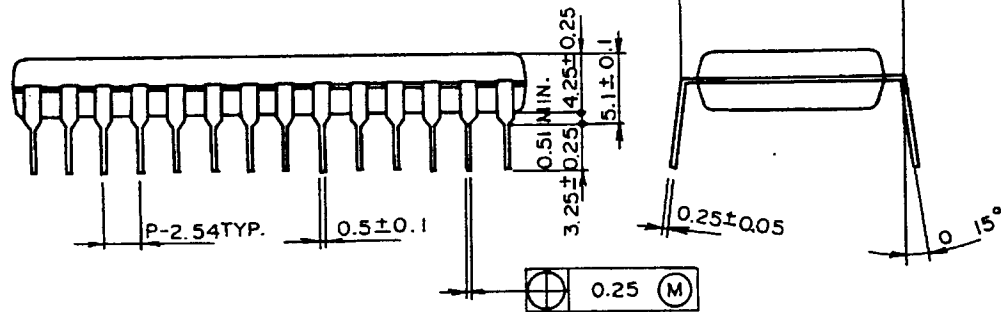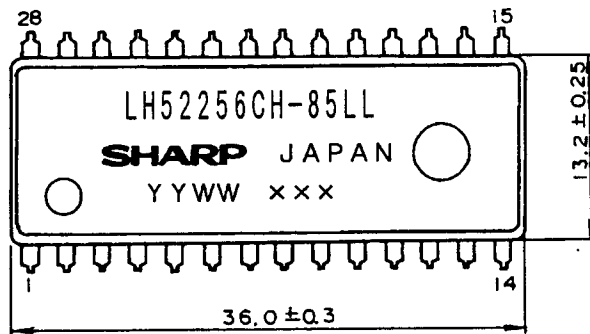4. Precaution For Unpacking
    (1) Unpacking should be done on the stand as well as human body treated with anti-ESD.
   (2) Anti-ESD treatment is given to a magazine.
        Use the equivalent magazine , if it is changed to another one.
    (3) Be sure to fix two stoppers to both ends of a magazine when storage to prevent the devices from slipping.

Solder dipping	245℃ or less, duration of less than 5 seconds/dip, total of 5 seconds. (Only the appropriate parts of leads for soldering are immersed in the surface of a jet stream solder bath. During soldering, the solder stream must not come into direct contact with the plastic body of package.)	Solder area.
Manual soldering (soldering iron)	260℃ or less, duration of less than 10 seconds. (Only the appropriate parts of leads for soldering are soldered with a soldering iron. During soldering, the soldering iron must not come into direct contact with the plastic body of package.)	IC outer lead surface.

LH52256CH-85LL

SHARP JAPAN

YYWW ×××

13.2±0.25

36.0±0.3

15.24 TYP.

4.25±0.25

0.51 MIN.

4.25±0.25

5.1±0.1

3.25±0.25

P-2.54TYP.

0.5±0.1

0.25±0.05

0.25 (M)

0° 15°

名称 NAME	DIP28-P-600	リード仕上 LEAD FINISH	TIN-LEAD PLATING	備考 NOTE	プラスチックパッケージ外形寸法は、バリを含まないものとする。 Plastic body dimensions do not include burr of resin.
DRAWING NO.	AA852	単位 UNIT	mm		

560.0 ±⅔

20.0

10.2

11.4

8-(R0.7)

5.5 ±⅓
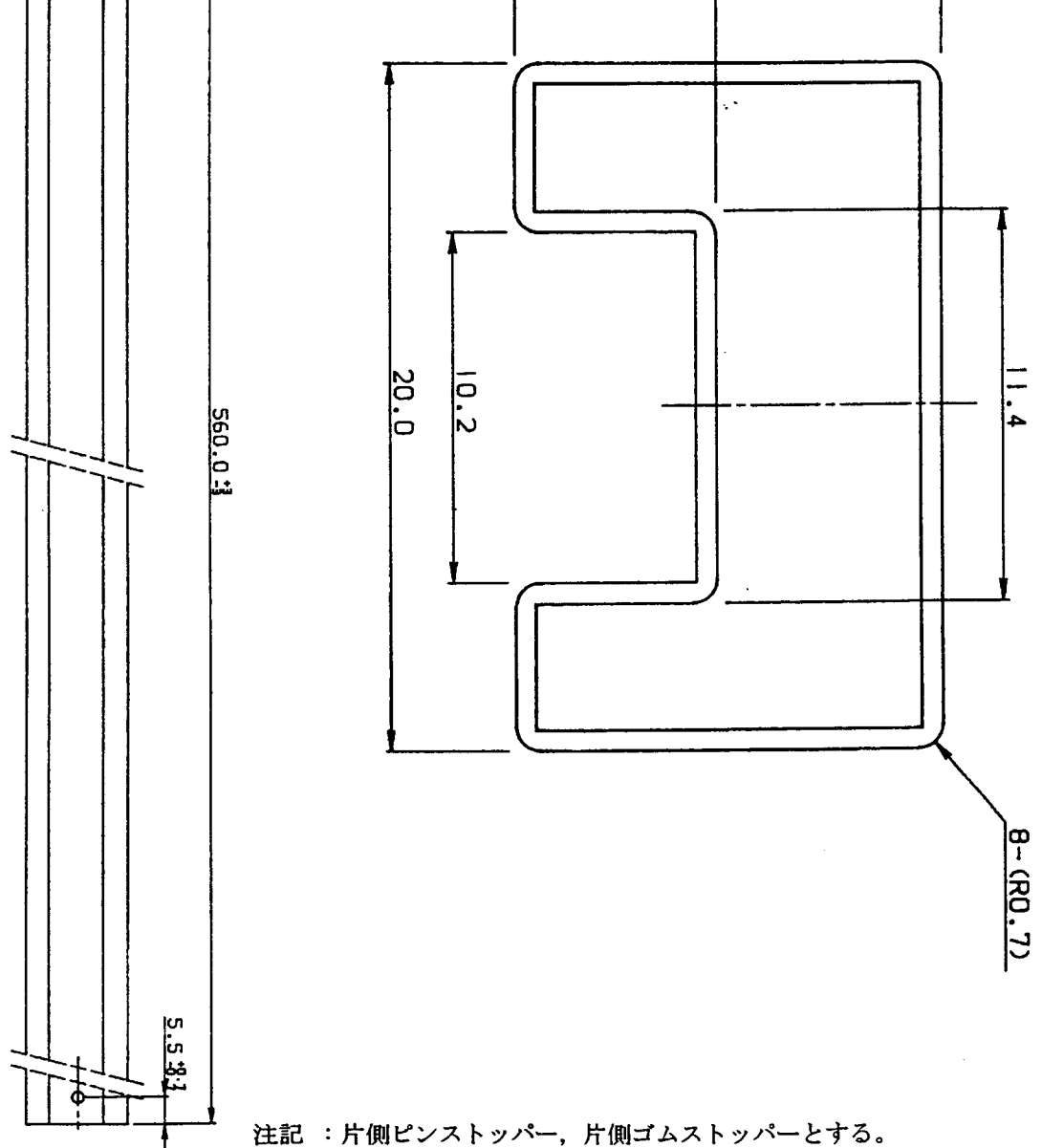
注記 ：片側ピンストッパー，片側ゴムストッパーとする。
　　　 指示無き寸法公差は全て±０．４とする。
NOTES : One end of magazine (sleeve) is plugged by stopper which is
　　　　 made of rubber, and another end of magazine (sleeve) is
　　　　 plugged by plastic pin-stopper.
　　　　 All tolerances are ±0.4mm　unless otherwise specified

名称 NAME	ＤＰ６００ＳＰＫ－Ａ２		備考 NOTE	
DRAWING NO.	CV651	単位 UNIT	mm	

Static SRAM RAM Random Access Memory LH52256CH-85LL 256K (32Kx8) (85 ns) (DIP)